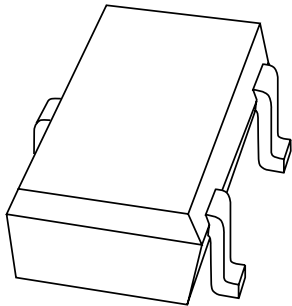


# DATA SHEET



## **PMST2222; PMST2222A** NPN switching transistors

Product data sheet  
Supersedes data of 1997 Jul 14

1999 Apr 22

# NPN switching transistors

# PMST2222; PMST2222A

### FEATURES

- High current (max. 600 mA)
- Low voltage (max. 40 V).

### APPLICATIONS

- High-speed switching and linear amplification.

### DESCRIPTION

NPN switching transistor in a SOT323 plastic package.  
PNP complement: PMST2907A.

### MARKING

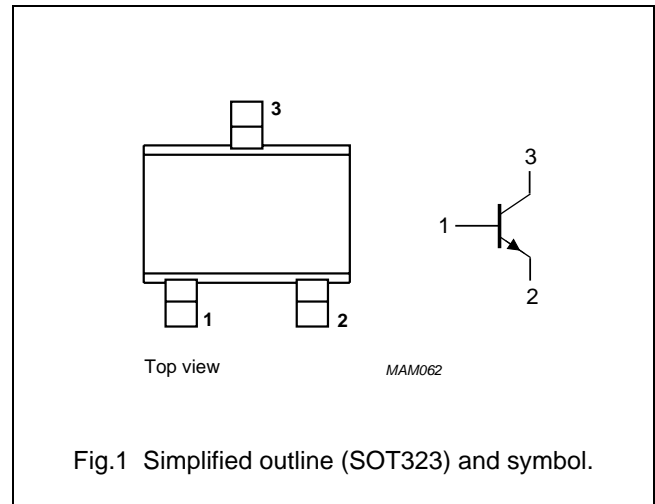
TYPE NUMBER	MARKING CODE <sup>(1)</sup>
PMST2222	*1B
PMST2222A	*1P

### Note

- \* = - : Made in Hong Kong.  
\* = t : Made in Malaysia.

### PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter			
	PMST2222		–	60	V
	PMST2222A		–	75	V
$V_{CEO}$	collector-emitter voltage	open base			
	PMST2222		–	30	V
	PMST2222A		–	40	V
$V_{EBO}$	emitter-base voltage	open collector			
	PMST2222		–	5	V
	PMST2222A		–	6	V
$I_C$	collector current (DC)		–	600	mA
$I_{CM}$	peak collector current		–	800	mA
$I_{BM}$	peak base current		–	200	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 1	–	200	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
$T_{amb}$	operating ambient temperature		–65	+150	°C

### Note

1. Transistor mounted on an FR4 printed-circuit board.

## NPN switching transistors

## PMST2222; PMST2222A

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	625	K/W

## Note

1. Transistor mounted on an FR4 printed-circuit board.

## CHARACTERISTICS

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{CBO}$	collector cut-off current PMST2222	$I_E = 0; V_{CB} = 50\text{ V}$	–	10	nA
		$I_E = 0; V_{CB} = 50\text{ V}; T_j = 125\text{ °C}$	–	10	$\mu\text{A}$
	collector cut-off current PMST2222A	$I_E = 0; V_{CB} = 60\text{ V}$	–	10	nA
		$I_E = 0; V_{CB} = 60\text{ V}; T_j = 125\text{ °C}$	–	10	$\mu\text{A}$
$I_{EBO}$	collector cut-off current	$I_C = 0; V_{EB} = 3\text{ V}$	–	10	nA
$h_{FE}$	DC current gain	$I_C = 0.1\text{ mA}; V_{CE} = 10\text{ V}$	35	–	
		$I_C = 1\text{ mA}; V_{CE} = 10\text{ V}$	50	–	
		$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}$	75	–	
		$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; T_{amb} = -55\text{ °C}$	35	–	
		$I_C = 150\text{ mA}; V_{CE} = 1\text{ V}; \text{note 1}$	50	–	
		$I_C = 150\text{ mA}; V_{CE} = 10\text{ V}; \text{note 1}$	100	300	
	DC current gain PMST2222 PMST2222A	$I_C = 500\text{ mA}; V_{CE} = 10\text{ V}; \text{note 1}$	30 40	– –	
$V_{CEsat}$	collector-emitter saturation voltage PMST2222	$I_C = 150\text{ mA}; I_B = 15\text{ mA}; \text{note 1}$	–	400	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	1.6	V
	collector-emitter saturation voltage PMST2222A	$I_C = 150\text{ mA}; I_B = 15\text{ mA}; \text{note 1}$	–	300	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	1	V
$V_{BEsat}$	base-emitter saturation voltage PMST2222	$I_C = 150\text{ mA}; I_B = 15\text{ mA}; \text{note 1}$	–	1.3	V
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	2.6	V
	base-emitter saturation voltage PMST2222A	$I_C = 150\text{ mA}; I_B = 15\text{ mA}; \text{note 1}$	0.6	1.2	V
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	2	V
$C_c$	collector capacitance	$I_E = i_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	8	pF
$C_e$	emitter capacitance PMST2222	$I_C = i_c = 0; V_{EB} = 0.5\text{ V}; f = 1\text{ MHz}$	–	30	pF
	PMST2222A		–	25	pF
$f_T$	transition frequency PMST2222	$I_C = 20\text{ mA}; V_{CE} = 20\text{ V}; f = 100\text{ MHz}$	250	–	MHz
	PMST2222A		300	–	MHz

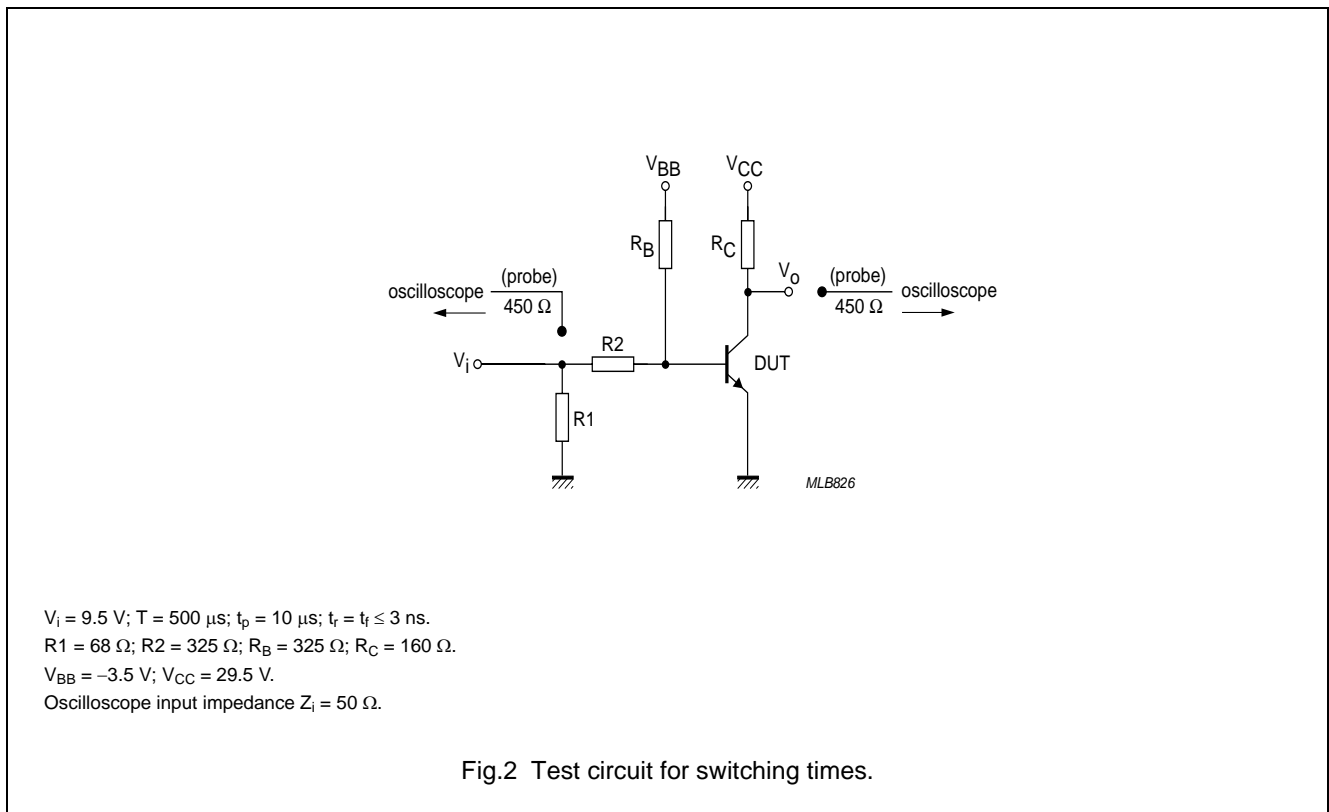
NPN switching transistors

PMST2222; PMST2222A

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
F	noise figure	$I_C = 200 \mu\text{A}$ ; $V_{CE} = 5 \text{ V}$ ; $R_S = 2 \text{ k}\Omega$ ; $f = 1 \text{ kHz}$ ; $B = 200 \text{ Hz}$	–	4	dB
<b>Switching times (between 10% and 90% levels); (see Fig.2)</b>					
$t_{on}$	turn-on time	$I_{Con} = 150 \text{ mA}$ ; $I_{Bon} = 15 \text{ mA}$ ; $I_{Boff} = -15 \text{ mA}$	–	35	ns
$t_d$	delay time		–	15	ns
$t_r$	rise time		–	20	ns
$t_{off}$	turn-off time		–	250	ns
$t_s$	storage time		–	200	ns
$t_f$	fall time		–	60	ns

Note

1. Pulse test:  $t_p \leq 300 \mu\text{s}$ ;  $\delta \leq 0.02$ .



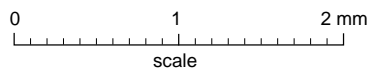
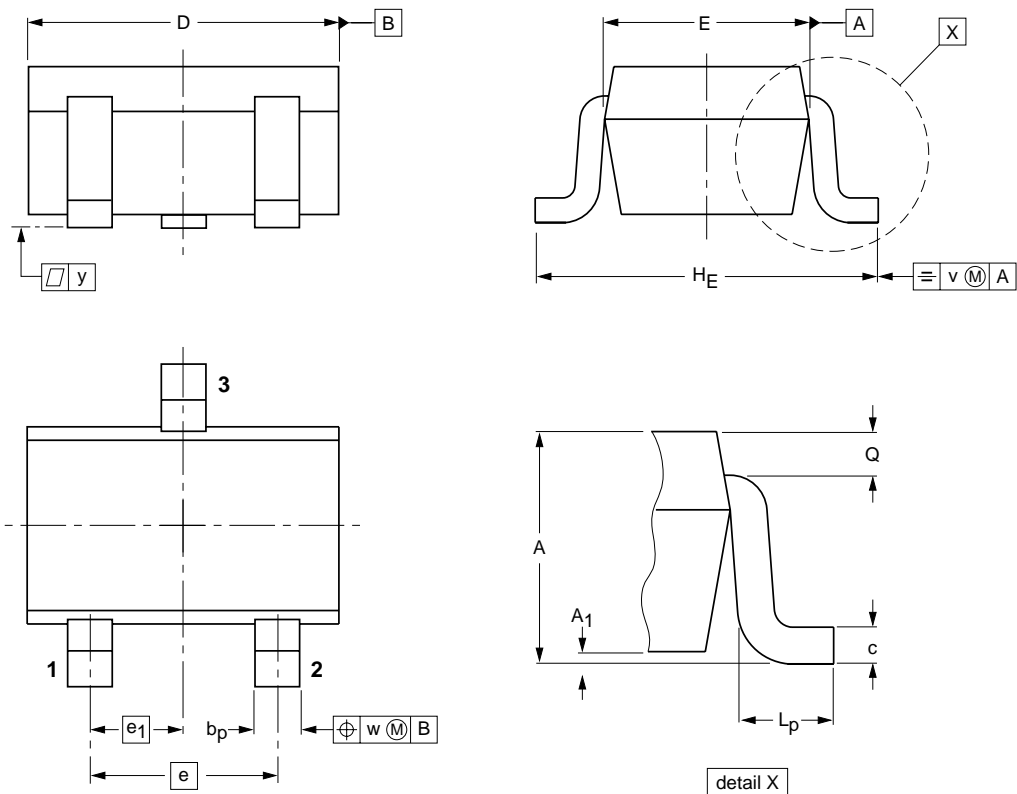
NPN switching transistors

PMST2222; PMST2222A

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT323			SC-70		97-02-28

## NPN switching transistors

PMST2222;  
PMST2222A

## DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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# ***NXP Semiconductors***

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